

ABSTRACT

A method for forming a double density wordline. A semiconductor substrate having a poly layer, a first insulating layer, a first dummy poly layer, and a second insulating layer is provided. The second insulating layer and the first dummy poly layer separated by an opening are a first wordline mask and a second wordline mask respectively. A spacer is formed on a sidewall of the opening, and the opening is filled with a second dummy poly layer. The spacer, the second insulating layer, and the exposed first insulating layer are removed to form a third wordline mask, the third wordline is composed of the second dummy poly layer and the unexposed first insulating layer. The poly layer is etched to form a first wordline, a second wordline, and a third wordline using the first wordline mask, the second wordline mask, and the third wordline mask as etching masks.